

64. The field effect transistor of claim 22 further including a raised epitaxial channel on said substrate, said raised epitaxial channel formed between said semiconductor regions forming said source and drain.

DRAWING

Enclosed is the drawing consisting of sheets 1-8 containing Figs. 1-25. Sheets 1-6 were in the prior application and contained Figs. 1-20. Sheets 7 and 8 are new and contain Figs. 21-25.

REMARKS

An inventor, Katherine L. Saenger, has been added to the named inventors of this application.

Enclosed is a copy of the prior specification as filed in the parent application.

Several typographical errors have been corrected in the specification.

New material has been added to the specification to expand the scope of the invention.

Sheets 7 and 8 containing Figs. 21-25 have been added to the drawing of the prior application which consisted of sheets 1-6.

Claim 23 has been amended to conform with amended claim 23 in the prior application.

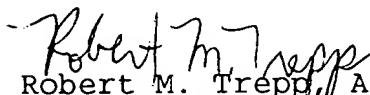
New claims 37-62 have been added to claim additional subject matter added to the specification by the instant continuation-in-part application.

Claims 37 and 38 submitted by amendment in the prior application now correspond to claims 63 and 64 respectively.

Enclosed is an Information Disclosure Statement containing a copy of PTO form 1449 submitted in the prior application.

Further favorable action and allowance of the claims is earnestly requested.

Respectfully submitted,


Robert M. Trepp, Attorney
Reg. No. 25,933

IBM Corporation
Intellectual Property Law Dept.
P.O. Box 218
Yorktown Heights, NY 10598
Telephone No. (914) 945-3147
Fax. No. (914) 945-3281